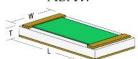
MICROWAVE CHIP RESISTORS

MSMW



Wire bondable gold OR Solderable gold with nickel barrier OR Nickel barrier pre-soldered

Mini-Systems, Inc. Top Contact Microwave Chip Resistor series is designed to fit a wide variety of applications operating in the Microwave Bands. All sizes offer the high stability, flat frequency response and low noise of Mini-Systems, Inc. Thin Film materials. Specialized LASER trim techniques specifically designed for this series guarantee operation up to 40 GHz. Microwave Chip Resistors can be attached to associated circuitry through ribbon or wire bonding, conductive epoxy, soldering to terminations or mounted as flip-chips.

GENERAL CHARACTERISTICS

Resistance Range	2Ω to $5k\Omega$					
Resistance Tolerance	±0.5% to ±10%					
Termination ¹	(G) Non-Solderable Gold, (NU) Soldereable Au w/ Ni barrier, (NT) Nickel with Solder					
Backing Material	Bare Substrate (Standard), Gold (Optional)					
Operating Temperature						
Storage Temperature		-65°C to +150°C				
Operating Voltage						
VSWR ²	DC to 10GHz 10 to 20GHz 20-40GHz					
15.1.1	1.2:1	1.3:1	1.5:1			

¹ Soldered or Solderable Gold require a Nickel Barrier

SUBSTRATE CHARACTERISTICS

	Available	Dielectric	Thermal	Current Noise			
SUBSTRATE	Thickness	Constant @ 1MHz	Conductivity W/m• K	101Ω to 5kΩ	≤ 100Ω		
99.6% Alumina	0.005" - 0.025"	9.9	28	-35dB	-30dB		
Beryllium Oxide	0.010" - 0.025"	6.7	300	-35dB	-30dB		
Aluminum Nitride	0.010" - 0.025"						
Quartz	0.005" - 0.010"	3.75	1.3	-40dB	-30dB		

RESISTOR CHARACTERISTICS

RESISTOR FILM	Passivation	Standard TCR	TCR Optional to:	
Tatalum Nitride	Ta ₂ O ₅ (Self Passivating)	±150 ppm/°C	±25 ppm/°C	
NiChrome	SiO ₂	±25 ppm/°C	±5 ppm/°C	

PART NUMBER DESIGNATION

MSMW STYLE	— 110 TYPE	— A SUBSTRATE	N — RESISTOR FILM	10000 OHMIC VALUE	F TOLERANCE		GGB OPTION
MSMW	SEE TABLE	A = Alumina B = BeO N = AlN Q = Quartz ³	T = Tantalum Nitride N = NiChrome		$D = \pm 0.5\%$ $F = \pm 1\%$ $G = \pm 2\%$ $J = \pm 5\%$ $K = \pm 10\%$	C = : B = : A = : F = :	±5ppm/°C ±10ppm/°C ±25ppm/°C ±50ppm/°C ±100ppm/°C Non-Solderable Gold
EXAMPLE:	MSMW-110 S Gold Backsid	e		r Film, $1 \mathrm{k}\Omega$, $\pm 1\%$ Tol., Non-Solo	lerable Gold,	NU = 3 NT = 1 NT3 = 1 GB = 0	Soldereable Au w/ Ni barrier Nickel w/ Sn62 Solder Nickel w/ SAC305 Solder Gold Back
³ Quartz ava	ilable as wire l	oondable only				TR = '	Tape & Reel

³ Quartz available as wire bondable only



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² Achieving operating characteristics is dependent on attachment methods in order to minimize parasitics

TOP CONTACT MICROWAVE CHIP RESISTORS

		I	DIMENSION	S		Max.		POWER	RATING ²	
CASE SIZE	ТҮРЕ	L (±0.002") [±0.051mm]	W (±0.002") [±0.051mm]	T ³ (±0.002") [±0.051mm]	Resistance Range	Operating Frequency ¹ GHz	Quartz	Alumina	AIN	BeO
0101	101									400mW
0201	21	0.020" [0.508]	0.010" [0.254]	0.006" [0.152]	3Ω - 400Ω	40	10mW	50mW	200mW	400mW
0202	1									400mW
0202	122	0.020" [0.508]	0.016" [0.406]	0.010" [0.254]	2Ω - 360Ω	40	25mW	125mW	500mW	1W
0202	7									2W
0302	32	0.030" [0.762]	0.020" [0.508]	0.010" [0.254]	2Ω - 500Ω	40	50mW	250mW	1W	2W
0402	110									1W
0404	2	0.035" [0.889]	0.035" [0.889]	0.010" [0.254]	2Ω - 1kΩ	26	50mW	250mW	1W	2W
0502	115									2W
0505	112	0.050" [1.270]	0.050" [1.270]	0.010" [0.254]	2Ω - 2kΩ	26	100mW	500mW	2W	4W
0603	8									2W
0805	3	0.075" [1.905]	0.050" [1.270]	0.010" [0.254]	2Ω - 3kΩ	26	100mW	500mW	2W	4W
1005	120									4W
1010	121	0.100" [2.540]	0.100" [2.540]	0.010" [0.254]	10Ω - 5kΩ	26	150mW	750mW	3W	6W
1206	5									

$MSMW\ 118\ will\ continue\ to\ be\ available,\ size\ and\ characteristics\ similar\ to\ MSMW122$

PERFORMANCE SPECIFICATIONS

PROPERTY	TEST CONDITION	REQUIRED LIMITS	MSI TYPICAL LIMITS
SHORT TERM OVERLOAD	2.5xWVDC(6.25xRATED POWER)MIL-PRF-55342, +25°C, 5 SEC	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
HIGH TEMP EXPOSURE	+150°C, 100HRS	±0.20 MAX ΔR/R	±0.03 MAX ΔR/R
THERMAL SHOCK	MIL-STD 202, METHOD 107	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
MOISTURE RESISTANCE	MIL-STD 202, METHOD 106	±0.40 MAX ΔR/R	±0.10 MAX ΔR/R
STABILITY	MIL-STD 202 METHOD 108, 2000 HRS, +70°C, RATED POWER	±0.50 MAX ΔR/R	±0.10 MAX ΔR/R

All MSMW Series parts are produced on the same manufacturing line using the same materials and processes as parts manufactured to MIL-PRF-55342



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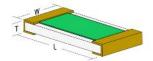
¹ Achieving operating characteristics in this frequency range is dependent on attachment methods in order to minimize parasitics

² Power rating at 70°C derated linearly to 0% at 150°C

³ Thickness does not include solder

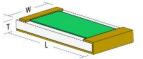
MICROWAVE CHIP RESISTORS

Wrap Around (WAMT)



Solderable gold with nickel barrier OR Nickel barrier pre-soldered

Half Wrap (HWMT)



Solderable gold with nickel barrier OR Nickel barrier pre-soldered Isolated pad is wire bondable

Mini-Systems, Inc. **Surface Mount Microwave Chip Resistor** series is designed to fit a wide variety of applications operating in the Microwave Bands. All sizes are offered in wrap around and half wrap configurations and offer the **high stability, flat frequency response** and **low noise** of Mini-Systems, Inc. Thin Film materials. **Specialized LASER trim** techniques specifically designed for this series guarantee operation up to **40 GHz**. Microwave Chip Resistors can be attached to associated circuitry through ribbon or wire bonding, conductive epoxy, or soldering to terminations.

GENERAL CHARACTERISTICS

Resistance Range	2Ω to $5\mathrm{k}\Omega$							
Resistance Tolerance	±0.5% to ±10%							
Termination ¹	(NU) Soldereable Au w/ Ni barrier, (NT) Nickel with Solder							
Operating Temperature	-55°C to +150°C							
Storage Temperature								
Operating Voltage		100V Max.						
VSWR ²	DC to 10GHz		20-40GHz					
	1.2:1							

¹ Soldered or Solderable Gold require a Nickel Barrier

SUBSTRATE CHARACTERISTICS

	Available	Dielectric	Thermal	Curren	ıt Noise
SUBSTRATE	Thickness	Constant @ 1MHz	Conductivity W/m• K	101Ω to $5k\Omega$	≤ 100Ω
99.6% Alumina	0.005" - 0.025"	9.9	28	-35dB	-30dB
Beryllium Oxide	0.010" - 0.025"	6.7	300	-35dB	-30dB
Aluminum Nitride	0.010" - 0.025"				

RESISTOR CHARACTERISTICS

RESISTOR FILM	Passivation	Standard TCR	TCR Optional to:	
Tatalum Nitride	Ta ₂ O ₅ (Self Passivating)	±150 ppm/°C	±25 ppm/°C	
NiChrome	SiO ₂	±25 ppm/°C	±5 ppm/°C	

PART NUMBER DESIGNATION

WAMT	- 4	_ <u>A</u>	<u> </u>	10000	F		GB
STYLE	TYPE	SUBSTRATE	RESISTOR FILM	OHMIC VALUE	TOLERANCE		OPTION
WAMT	SEE	A = Alumina	T = Tantalum Nitride	5-Digit Number:	$D = \pm 0.5\%$	D	= ±5ppm/°C
HWMT	TABLE	B = BeO	N = NiChrome	1st 4 digits are significant	$F = \pm 1\%$	C	= ±10ppm/°C
		N = AlN		with "R" as decimal point	$G = \pm 2\%$	В	= ±25ppm/°C
				when required. 5th digit	$J = \pm 5\%$	Α	= ±50ppm/°C
				represents number of zeros.	$K = \pm 10\%$	F	= ±100ppm/°C
						NU	= Soldereable Au w/ Ni barrie
EXAMPLE:	WAMT- 4 - A	N - 10000F - NT				NT	= Nickel w/ Sn62 Solder
	WAMT-4 Ser	ies, Alumina Substra	ate, NiChrome Resistor Fi	lm, 1kΩ, ±1% Tol., Nickel w/ Si	n62 Solder	NT	3 = Nickel w/ SAC305 Solder
		,	,	, ,,		TR	= Tape & Reel



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² Achieving operating characteristics is dependent on attachment methods in order to minimize parasitics

SURFACE MOUNT MICROWAVE CHIP RESISTORS

			DIMENSIONS			Max.	ı	POWER RATING	2
CASE SIZE	ТҮРЕ	L (±0.002") [±0.051mm]	W (±0.002") [±0.051mm]	T ³ (±0.002") [±0.051mm]	Resistance Range	Operating Frequency ¹ GHz	Alumina	AlN	BeO
0201	21	0,020" [0.508]	0.010" [0.254]	0,006" [0.152]	3Ω - 400Ω	20	50mW	200mW	400mW
0202	122	0.020" [0.508]	0.016" [0.406]	0.010" [0.254]	2Ω - 360Ω	20	125mW	500mW	1W
0202									
0302	32	0 . 030" [0.762]	0.020" [0.508]	0.010" [0.254]	2Ω - 500Ω	20	250mW	1W	2W
0402									
0404	2	0.035" [0.889]	0.035" [0.889]	0.010" [0.254]	2Ω - 1kΩ	13	250mW	1W	2W
0502									
0505	4	0.050" [1.270]	0.050" [1.270]	0.010" [0.254]	2Ω - 2kΩ	13	500mW	2W	4W
0603									
0805	3	0.075" [1.905]	0.050" [1.270]	0.010" [0.254]	2Ω - 3kΩ	13	500mW	2W	4W
1005									
1010	121	0.100" [2.540]	0.100" [2.540]	0.010" [0.254]	10Ω - 5kΩ	13	750mW	3W	6W
1206									

¹ Achieving operating characteristics in this frequency range is dependent on attachment methods in order to minimize parasitics

PERFORMANCE SPECIFICATIONS

PROPERTY	TEST CONDITION	REQUIRED LIMITS	MSI TYPICAL LIMITS
SHORT TERM OVERLOAD	2.5xWVDC(6.25xRATED POWER)MIL-PRF-55342, +25°C, 5 SEC	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
HIGH TEMP EXPOSURE	+150°C, 100HRS	±0.20 MAX ΔR/R	±0.03 MAX ΔR/R
THERMAL SHOCK	MIL-STD 202, METHOD 107	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
MOISTURE RESISTANCE	MIL-STD 202, METHOD 106	±0.40 MAX ΔR/R	±0.10 MAX ΔR/R
STABILITY	MIL-STD 202 METHOD 108, 2000 HRS, +70°C, RATED POWER	±0.50 MAX ΔR/R	±0.10 MAX ΔR/R

All WAMT, HWMT Series parts are produced on the same manufacturing line using the same materials and processes as parts manufactured to MIL-PRF-55342



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² Power rating at 70°C derated linearly to 0% at 150°C

³ Thickness does not include solder